

Blend

forming a metallic film on the thin film resistor;
oxidizing a surface portion of the metallic film to form a surface oxide layer on the metallic film;
forming a conductive film on the surface oxide layer;
patterning the conductive film to form an opening in the conductive film, the opening exposing the surface oxide layer therefrom; and
wet-etching the surface oxide layer and the metallic film,
wherein the conductive film is made of a metallic material different from that of the metallic film, and
wherein the wet-etching is performed in a state where both the conductive film and the metallic film contact an etching solution.